

**Features**

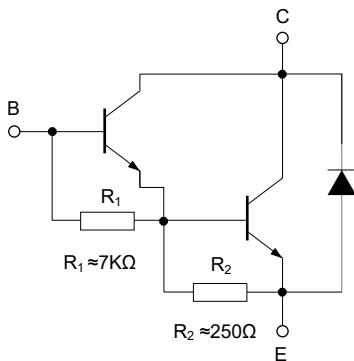
- High DC Current Gain
- Built-in a Damper Diode at E-C
- Halogen Free Available Upon Request By Adding Suffix "-HF"
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

**Maximum Ratings @ 25°C Unless Otherwise Specified**

- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 83°C/W Junction to Ambient

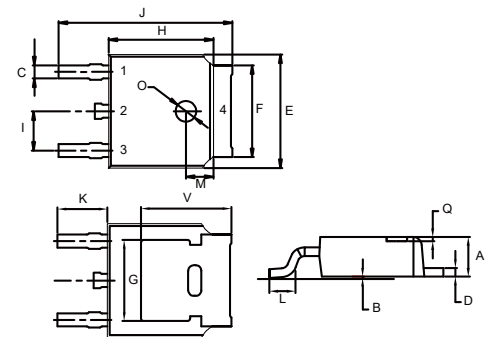
Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	$V_{CEO}$	100	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Continuous Collector Current	$I_C$	8	A
Power Dissipation	$P_D$	1.5	W

**Internal Schematic Diagram**



**Silicon  
NPN epitaxial planer  
Transistors**

**DPAK(TO-252)**



1.BASE  
2,4.COLLECTOR  
3.EMITTER

DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

**Electrical Characteristics @  $T_A=25^\circ\text{C}$  Unless Otherwise Specified**

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100			V	$I_C=1\text{mA}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	100			V	$I_C=30\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=3\text{mA}, I_C=0$
Collector Cutoff Current	$I_{CBO}$			10	$\mu\text{A}$	$V_{CB}=100\text{V}, I_E=0$
Collector Cutoff Current	$I_{CEO}$			10	$\mu\text{A}$	$V_{CE}=50\text{V}, I_B=0$
Emitter Cutoff Current	$I_{EBO}$			2	mA	$V_{EB}=5\text{V}, I_C=0$
DC Current Gain	$h_{FE(1)}$	1000		12000		$V_{CE}=4\text{V}, I_C=4\text{A}$
	$h_{FE(2)}$	100				$V_{CE}=4\text{V}, I_C=8\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			2.0	V	$I_C=4\text{A}, I_B=16\text{mA}$
				4.0	V	$I_C=8\text{A}, I_B=80\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			4.5	V	$I_C=8\text{A}, I_B=80\text{mA}$
Base-Emitter Voltage	$V_{BE}$			2.8	V	$V_{CE}=4\text{V}, I_C=4\text{A}$
Output Capacitance	$C_{ob}$			200	pF	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$

**Curve Characteristics**

Fig. 1 - Static Characteristics

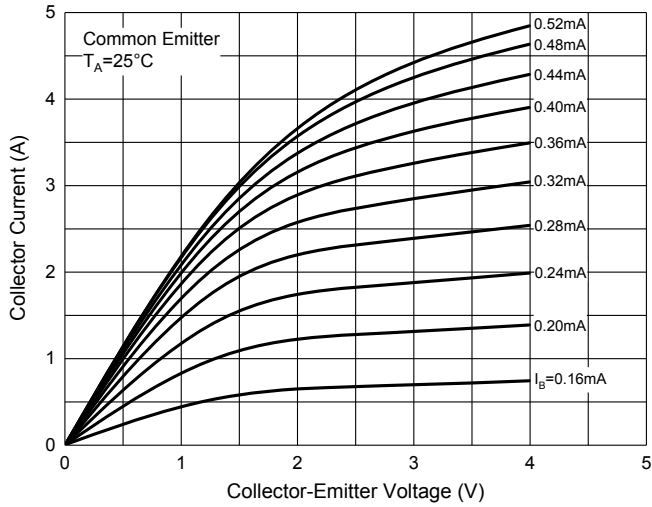


Fig. 2 - DC Current Gain Characteristics

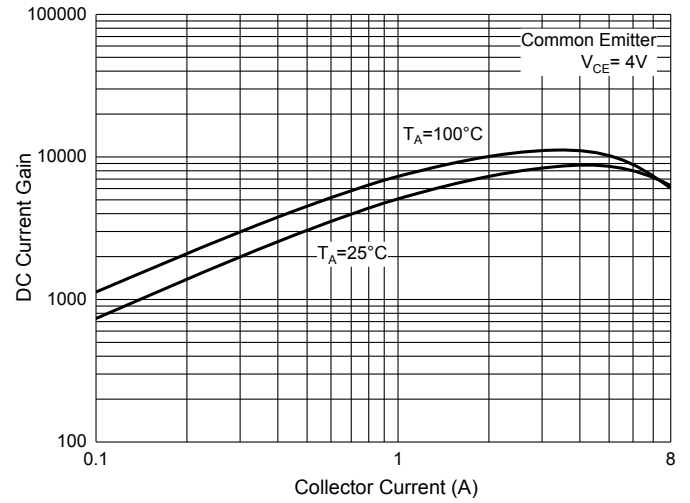


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

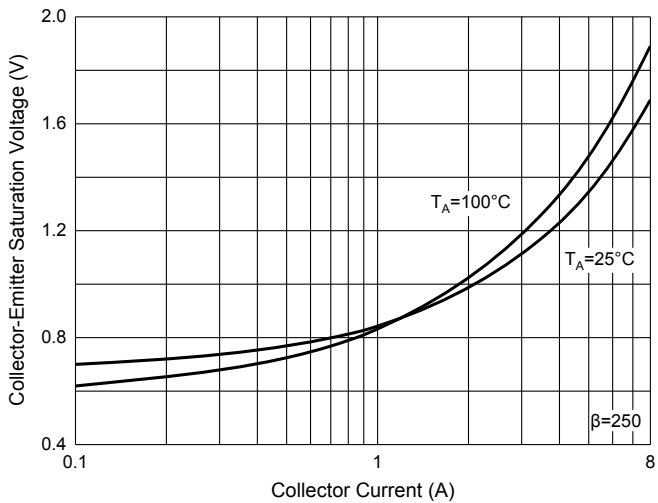


Fig. 4 - Collector-Emitter Saturation Voltage Characteristics

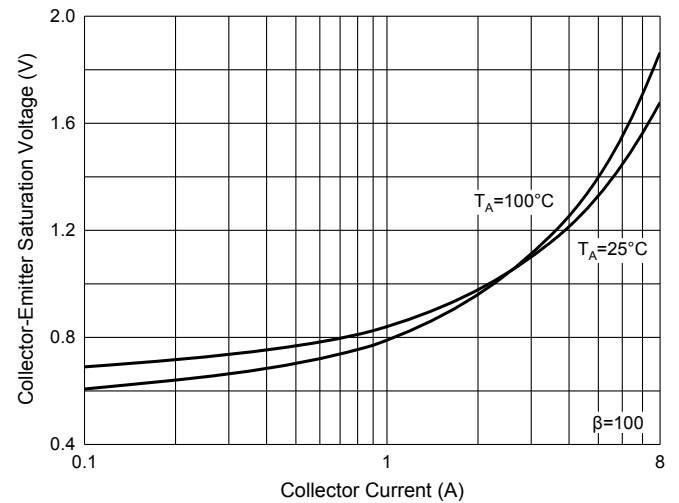


Fig. 5 - Base-Emitter Saturation Voltage Characteristics

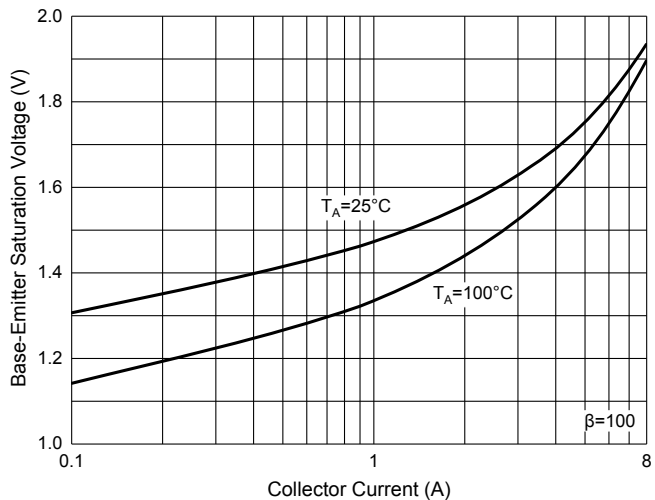


Fig. 6 - Collector Power Derating Curve

